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I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date shown below.

September 1, 2006

Signed Michelle Chan
Michelle Chan

Appl. No.	:	10/796,413 Confirmation No. 9041
Applicant	:	Xiangfeng Duan et al.
Filed	:	March 10, 2004
TC/A.U.	:	2891
Examiner	:	Matthew Reames
Docket No.	:	01-004100
Customer No.	:	33140
Title	:	Nano-enabled Memory Devices and Anisotropic Charge Carrying Arrays

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

The references cited on the attached form PTO/SB08A-B are being called to the attention of the Examiner. Pursuant to 37 CFR §1.98(a)(2), copies of all foreign patent documents and non US Patent and US Patent application publications are enclosed.

It is respectfully requested that the cited information be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

As provided for by 37 CFR §1.97(g) and (h), no inference should be made that the information and references cited are prior art merely because they are in this statement and no representation is made that a search has been conducted or that this statement encompasses all possible relevant information.

This information disclosure statement is being filed after the mailing date of the first Office Action and more than three months after the filing date, but prior to the mailing of a Notice of Allowance or Final Office Action. Authorization to charge the appropriate fee to the undersigned's deposit account is submitted herewith. Please charge any additional fees or credit any overpayment to Deposit Account No. 50-2336.

Respectfully submitted,

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(Modified) PTO/SB/08A-B (08-03)
Approved for use through 7/31/2006. OMB 0651-0031

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	**10/796,413**
				Filing Date	**March 10, 2004**
				First Named Inventor	**Duan**
				Art Unit	**2891**
(use as many sheets as necessary)				Examiner Name	**Matthew Reames**
Sheet		of		Attorney Docket Number	**01-004100**

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Examiner Initials	Cite No.	Document No. Number - Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, lines, Where Relevant Passages or Relevant Figures Appeal
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Examiner Initials	Cite No.	Foreign Patent Document Country Code - Number - Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
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	AU	WO-0248701	06-20-2002	Harvard		
	AV	WO-2005017962	02-24-2005	Nanosys		

Examiner Signature		Date Considered	

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(use as many sheets as necessary)				Examiner Name	**Matthew Reames**
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and-or country where published.	T
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	BK		
	BL		

Examiner Signature		Date Considered	

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